Integrated Device Technology, Inc.

HIGH-SPEED 2K x 8 FourPort™ STATIC RAM

PRELIMINARY
IDT7052S
IDT7052L

FEATURES:

- High-speed access
  - — Military: 30/35/45ns (max.)
  - — Commercial: 25/30/35/45ns (max.)
- Low-power operation
  - — IDT7052S
    Active: 750mW (typ.)
    Standby: 10mW (typ.)
  - — IDT7052L
    Active: 750mW (typ.)
    Standby: 1.5mW (typ.)
- Fully asynchronous operation from each of the four ports: P1, P2, P3, P4
- Versatile control for write-inhibit: separate $\overline{BUSY}$ input to control write-inhibit for each of the four ports
- Battery backup operation—2V data retention
- TTL-compatible; single 5V (±10%) power supply
- Available in several popular hermetic and plastic packages for both through-hole and surface mount
- Military product compliant to MIL-STD-883, Class B

DESCRIPTION:

The IDT7052 is a high-speed 2K x 8 FourPort static RAM designed to be used in systems where multiple access in a common RAM is required. This FourPort static RAM offers increased system performance in multiprocessed systems that have a need to communicate in real time and also offers added benefit for high-speed systems in which multiple access is required in the same cycle.

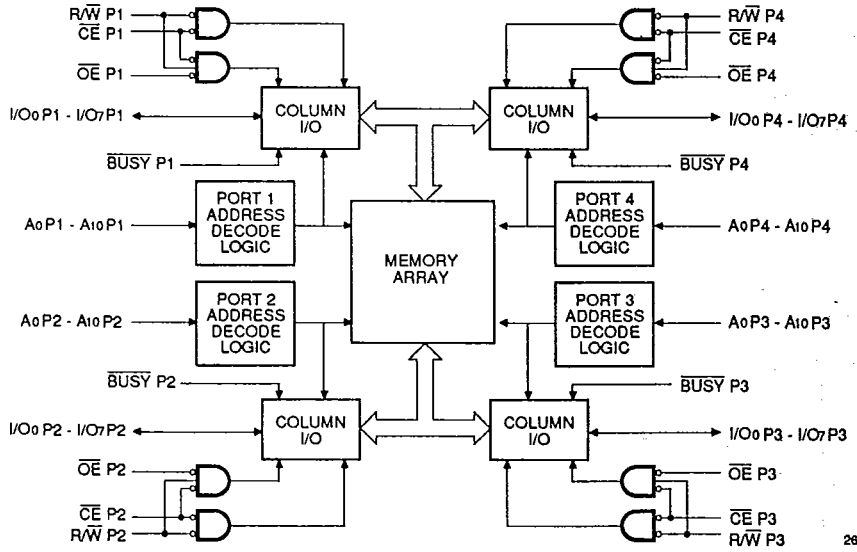
The IDT7052 is also an extremely high-speed 2K x 8 FourPort static RAM designed to be used in systems where on-chip hardware port arbitration is not needed. This part lends itself to those systems which cannot tolerate wait states or are designed to be able to externally arbitrate or withstand contention when all ports simultaneously access the same FourPort RAM location.

The IDT7052 provides four independent ports with separate control, address and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. It is the user's responsibility to ensure data integrity when simultaneously accessing the same memory location from all ports. An automatic power down feature, controlled by $\overline{CE}$, permits the on-chip circuitry of each port to enter a very low power standby power mode.

Fabricated using IDT's CEMOS™ high-performance technology, this four port RAM typically operates on only 750mW of power at maximum access times as fast as 25ns. Low-power (L) versions offer battery backup data retention capability, with each port typically consuming 50µW from a 2V battery.

The IDT7052 is packaged in either a ceramic or plastic 108-pin PGA and 132-pin quad flatpack. Military grade product is manufactured in compliance with the latest revision of MIL-STD-883, Class B.

FUNCTIONAL BLOCK DIAGRAM

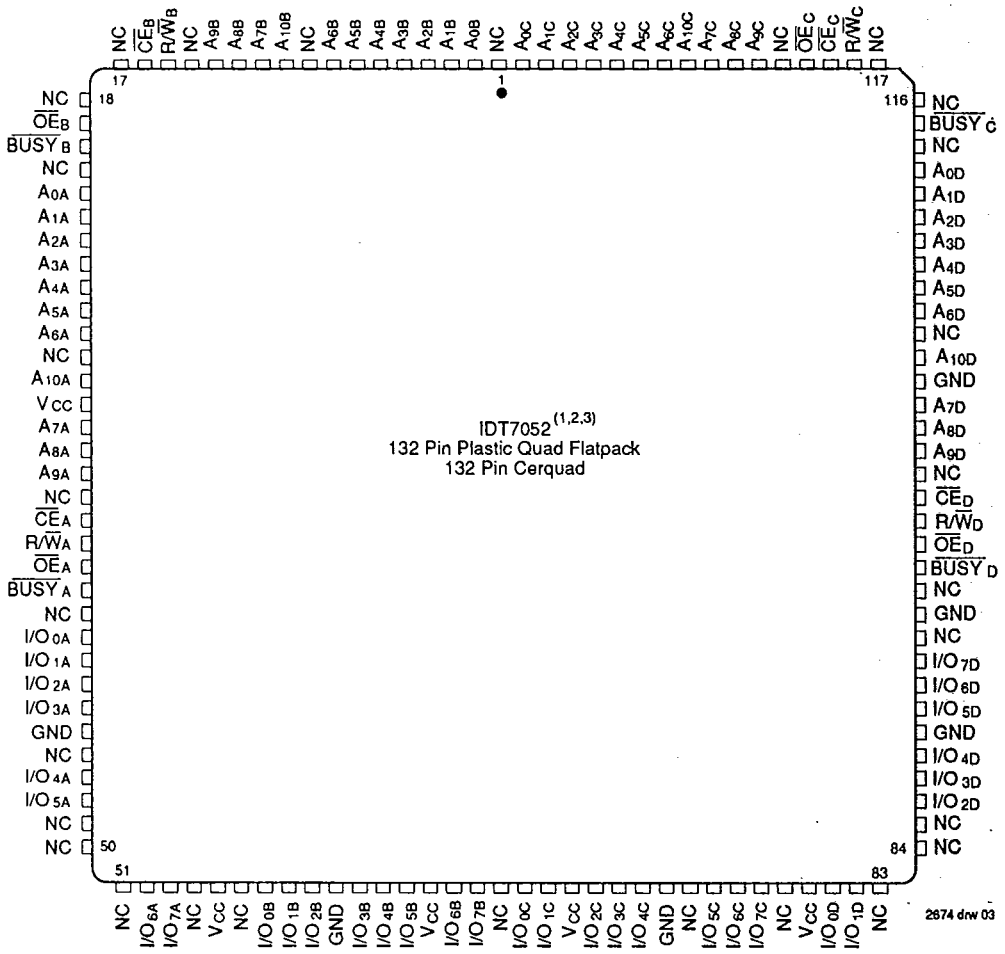


FourPort is a trademark of Integrated Device Technology, Inc.

81 $R/\overline{W}$ P2	80 NC	77 A_7 P2	74 A_5 P2	72 A_3 P2	69 A_0 P2	68 A_0 P3	65 A_3 P3	63 A_5 P3	60 A_7 P3	57 NC	54 $R/\overline{W}$ P3	12
84 $\overline{BUSY}$ P2	83 $\overline{OE}$ P2	78 A_8 P2	76 A_{10} P2	73 A_4 P2	70 A_1 P2	67 A_1 P3	64 A_4 P3	61 A_{10} P3	59 A_8 P3	56 $\overline{OE}$ P3	53 $\overline{BUSY}$ P3	11
87 A_2 P1	86 A_1 P1	82 $\overline{CE}$ P2	79 A_9 P2	75 A_6 P2	71 A_2 P2	66 A_2 P3	62 A_6 P3	58 A_9 P3	55 $\overline{CE}$ P3	51 A_1 P4	50 A_2 P4	10
90 A_5 P1	88 A_3 P1	85 A_0 P1							52 A_0 P4	49 A_3 P4	47 A_5 P4	09
92 A_{10} P1	91 A_6 P1	89 A_4 P1							48 A_4 P4	46 A_6 P4	45 A_{10} P4	08
95 A_8 P1	94 A_7 P1	93 V_{CC}			IDT7052 108-Pin PGA(1,2,3)				44 GND	43 A_7 P4	42 A_8 P4	07
96 A_9 P1	97 NC	98 $\overline{CE}$ P1			TOP VIEW				39 $\overline{CE}$ P4	40 NC	41 A_9 P4	06
99 $R/\overline{W}$ P1	100 $\overline{OE}$ P1	102 I/O_0 P1							35 GND	37 $\overline{OE}$ P4	38 $R/\overline{W}$ P4	05
101 $\overline{BUSY}$ P1	103 I/O_1 P1	106 GND							31 GND	34 I/O_7 P4	36 $\overline{BUSY}$ P4	04
104 I/O_2 P1	105 I/O_3 P1	1 I/O_6 P1	4 V_{CC}	8 GND	12 V_{CC}	17 V_{CC}	21 GND	25 V_{CC}	28 I/O_2 P4	32 I/O_5 P4	33 I/O_6 P4	03
107 I/O_4 P1	2 I/O_7 P1	5 I/O_0 P2	7 I/O_2 P2	10 I/O_4 P2	13 I/O_6 P2	16 I/O_1 P3	19 I/O_3 P3	22 I/O_5 P3	24 I/O_7 P3	29 I/O_3 P4	30 I/O_4 P4	02
108 I/O_5 P1	3 NC	6 I/O_1 P2	9 I/O_3 P2	11 I/O_5 P2	14 I/O_7 P2	15 I/O_0 P3	18 I/O_2 P3	20 I/O_4 P3	23 I/O_6 P3	26 I/O_0 P4	27 I/O_1 P4	01
A	B	C	D	E	F	G	H	J	K	L	M	

2674 drw 02

NOTES:
1. All Vcc pins must be connected to the power supply.
2. All GND pins must be connected to the ground supply.
3. NC denotes no-connect pin.



NOTES:
1. All Vcc pins must be connected to the power supply.
2. All GND pins must be connected to the ground supply.
3. NC denotes no-connect pin.

PIN CONFIGURATIONS

Symbol	Pin Name
A_0 P1 – A_{10} P1	Address Lines – Port 1
A_0 P2 – A_{10} P2	Address Lines – Port 2
A_0 P3 – A_{10} P3	Address Lines – Port 3
A_0 P4 – A_{10} P4	Address Lines – Port 4
I/O_0 P1 – I/O_7 P1	Data I/O – Port 1
I/O_0 P2 – I/O_7 P2	Data I/O – Port 2
I/O_0 P3 – I/O_7 P3	Data I/O – Port 3
I/O_0 P4 – I/O_7 P4	Data I/O – Port 4
$R/\overline{W}$ P1	Read/Write – Port 1
$R/\overline{W}$ P2	Read/Write – Port 2
$R/\overline{W}$ P3	Read/Write – Port 3
$R/\overline{W}$ P4	Read/Write – Port 4
GND	Ground
$\overline{CE}$ P1	Chip Enable – Port 1
$\overline{CE}$ P2	Chip Enable – Port 2
$\overline{CE}$ P3	Chip Enable – Port 3
$\overline{CE}$ P4	Chip Enable – Port 4
$\overline{OE}$ P1	Output Enable – Port 1
$\overline{OE}$ P2	Output Enable – Port 2
$\overline{OE}$ P3	Output Enable – Port 3
$\overline{OE}$ P4	Output Enable – Port 4
$\overline{BUSY}$ P1	Write Disable – Port 1
$\overline{BUSY}$ P2	Write Disable – Port 2
$\overline{BUSY}$ P3	Write Disable – Port 3
$\overline{BUSY}$ P4	Write Disable – Port 4
Vcc	Power
GND	Ground

2674 tbl 01

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Rating	Commercial	Military	Unit
V_{TERM}	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
T_A	Operating Temperature	0 to +70	-55 to +125	°C
T_{BIAS}	Temperature Under Bias	-55 to +125	-65 to +135	°C
T_{STG}	Storage Temperature	-55 to +125	-65 to +150	°C
I_{OUT}	DC Output Current	50	50	mA

NOTE: 2674 tbl 02

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

CAPACITANCE (T_A = +25°C, f = 1.0MHz)

Symbol	Parameter(1)	Conditions	Max.	Unit
C_{IN}	Input Capacitance	V_{IN} = 0V	11	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0V	11	pF

NOTE: 2674 tbl 03

1. This parameter is determined by device characterization but is not production tested.

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Grade	Ambient Temperature	GND	Vcc
Military	-55°C to +125°C	0V	5.0V ± 10%
Commercial	0°C to +70°C	0V	5.0V ± 10%

2674 tbl 04

RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min.	Typ.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
V_{IH}	Input High Voltage	2.2	—	6.0	V
V_{IL}	Input Low Voltage	-0.5(1)	—	0.8	V

NOTE: 2674 tbl 05

1. V_{IL} (min.) = -3.0V for pulse width less than 20ns.

DC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE (V_{CC} = 5.0V ± 10%)

Symbol	Parameter	Test Conditions	IDT7052S		IDT7052L		Unit
			Min.	Max.	Min.	Max.	
$\|I_{LI}\|$	Input Leakage Current	V_{CC} = 5.5V, V_{IN} = 0V to V_{CC}	—	10	—	5	µA
$\|I_{LO}\|$	Output Leakage Current	$\overline{CE}$ = V_{IH}, V_{OUT} = 0V to V_{CC}	—	10	—	5	µA
V_{OL}	Output Low Voltage	I_{OL} = 4mA	—	0.4	—	0.4	V
V_{OH}	Output High Voltage	I_{OH} = -4mA	2.4	—	2.4	—	V

2674 tbl 06

DC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE[1, 2, 6] (V_{CC} = 5.0V ± 10%)

Symbol	Parameter	Test Condition	Version		IDT7052x25[3]		IDT7052x30		IDT7052x35		IDT7052x45		Unit
					Typ.	Max.	Typ.	Max.	Typ.	Max.	Typ.	Max.	
I_{CC1}	Operating Power Supply Current (All Ports Active)	$\overline{CE}$ ≤ V_{IL} Outputs Open f = 0[4]	MIL.	S	—	—	150	360	150	360	150	360	mA
				L	—	—	150	300	150	300	150	300	
			COM'L.	S	150	300	150	300	150	300	150	300	
				L	150	250	150	250	150	250	150	250	
I_{CC2}	Dynamic Operating Current (All Ports Active)	$\overline{CE}$ ≤ V_{IL} Outputs Open f = f_{MAX}[5]	MIL.	S	—	—	220	400	210	395	195	390	mA
				L	—	—	190	335	180	330	170	325	
			COM'L.	S	225	350	220	340	210	335	195	330	
				L	195	305	190	295	180	290	170	285	
I_{SB}	Standby Current (All Ports — TTL Level Inputs)	$\overline{CE}$ ≥ V_{IH} f = f_{MAX}[5]	MIL.	S	—	—	45	115	40	110	35	105	mA
				L	—	—	40	85	35	80	30	75	
			COM'L.	S	60	85	45	80	40	75	35	70	
				L	50	70	40	65	35	60	30	55	
I_{SB1}	Full Standby Current (All Ports — All CMOS Level Inputs)	All Ports $\overline{CE}$ ≥ V_{CC} - 0.2V	MIL.	S	—	—	1.5	30	1.5	30	1.5	30	mA
				L	—	—	.3	4.5	.3	4.5	.3	4.5	
		V_{IN} ≥ V_{CC} - 0.2V or V_{IN} ≤ 0.2V, f = 0[4]	COM'L.	S	1.5	15	1.5	15	1.5	15	1.5	15	
				L	.3	1.5	.3	1.5	.3	1.5	.3	1.5	

2674 tbl 07

NOTES:
1. "x" in part number indicates power rating (S or L).
2. V_{CC} = 5V, T_A = +25°C for Typ.
3. 0°C to +70°C temperature range only.
4. f = 0 means no address or control lines change.
5. At f = f_{MAX}, address and data inputs (except Output Enable) are cycling at the maximum frequency of read cycle of 1/t_{RC}, and using "AC Test Conditions" of input levels of GND to 3V.
6. For the case of one port, divide the above appropriate current by four.

DATA RETENTION CHARACTERISTICS OVER ALL TEMPERATURE RANGES[1]

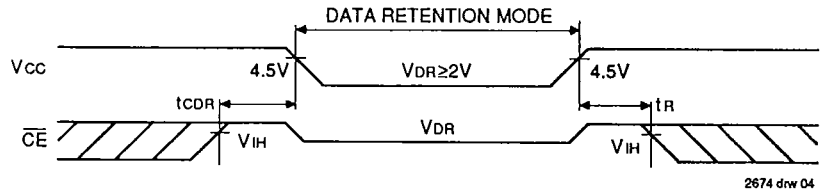
(L Version Only) V_{LC} = 0.2V, V_{HC} = V_{CC} - 0.2V

Symbol	Parameter	Test Condition		Min.	Typ.[1]	Max.	Unit
V_{DR}	V_{CC} for Data Retention	V_{CC} = 2V		2.0	—	—	V
I_{CCDR}	Data Retention Current	$\overline{CE}$ ≥ V_{HC}	MIL.	—	25	1800	µA
		V_{IN} ≥ V_{HC} or ≤ V_{LC}	COM'L.	—	25	600	
t_{CDR}[3]	Chip Deselect to Data Retention Time			0	—	—	ns
t_R[3]	Operation Recovery Time			t_{RC}[2]	—	—	ns

2674 tbl 08

NOTES:
1. V_{CC} = 2V, T_A = +25°C
2. t_{RC} = Read Cycle Time
3. This parameter is guaranteed but not tested.

LOW Vcc DATA RETENTION WAVEFORM



AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figures 1 & 2

2674 tbl 09

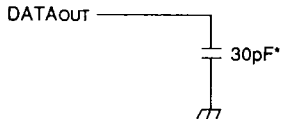


Figure 1. Output Load

*Including scope and jig

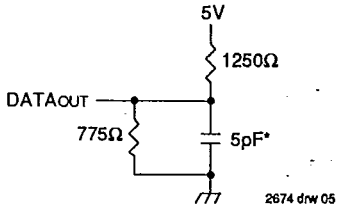


Figure 2. Output Load
(for tLZ, tHZ, tWZ, tOW)

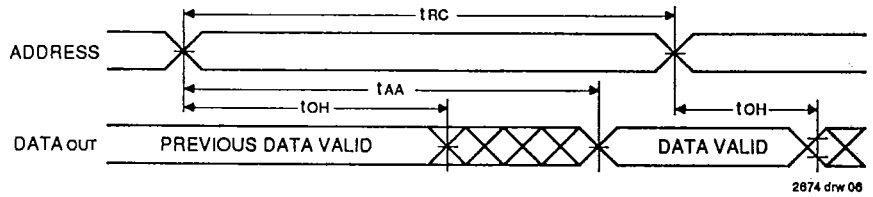
AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Symbol	Parameter	IDT7052S25[1] IDT7052L25[1] Min.	Max.	IDT7052S30 IDT7052L30 Min.	Max.	IDT7052S35 IDT7052L35 Min.	Max.	IDT7052S45 IDT7052L45 Min.	Max.	Unit
READ CYCLE										
tRC	Read Cycle Time	25	—	30	—	35	—	45	—	ns
tAA	Address Access Time	—	25	—	30	—	35	—	45	ns
tACE	Chip Enable Access Time	—	25	—	30	—	35	—	45	ns
tAOE	Output Enable Access Time	—	15	—	20	—	25	—	30	ns
tOH	Output Hold from Address Change	0	—	0	—	0	—	0	—	ns
tLZ	Output Low Z Time[1, 2]	3	—	3	—	5	—	5	—	ns
tHZ	Output High Z Time[1, 2]	—	15	—	15	—	15	—	20	ns
tPU	Chip Enable to Power Up Time[2]	0	—	0	—	0	—	0	—	ns
tPD	Chip Disable to Power Down Time[2]	—	20	—	30	—	50	—	50	ns

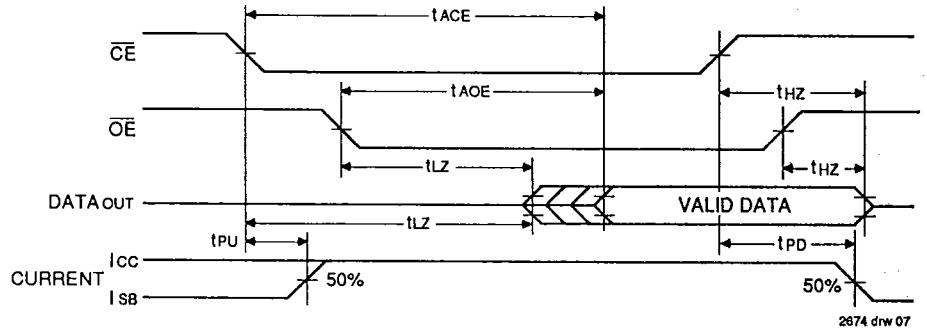
2674 tbl 10

NOTES:
1. Transition is measured ±500mV from low or high impedance voltage with load (Figures 1 and 2).
2. This parameter is guaranteed but not tested.
3. 0°C to +70°C temperature range only.

TIMING WAVEFORM OF READ CYCLE NO. 1, ANY PORT(1, 2, 4)



TIMING WAVEFORM OF READ CYCLE NO. 2, ANY PORT(1, 3)



NOTES:
1. R/W is high for Read Cycles.
2. Device is continuously enabled, CE = VIL.
3. Addresses valid prior to or coincident with CE transition low.
4. OE = VIL.

AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE

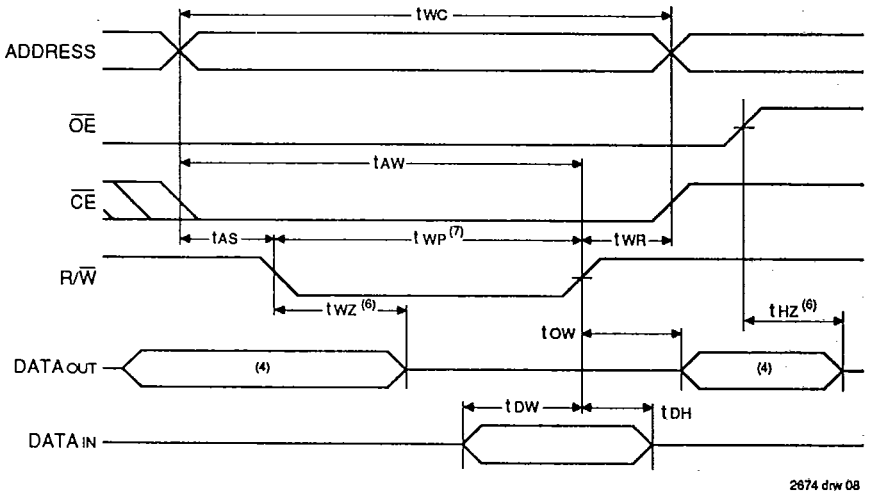
T-46-23-12

Symbol	Parameter	IDT7052S25[7] IDT7052L25[7] Min.	Max.	IDT7052S30 IDT7052L30 Min.	Max.	IDT7052S35 IDT7052L35 Min.	Max.	IDT7052S45 IDT7052L45 Min.	Max.	Unit
WRITE CYCLE										
tWC	Write Cycle Time	25	—	30	—	35	—	45	—	ns
tEW	Chip Enable to End of Write	20	—	25	—	30	—	35	—	ns
tAW	Address Valid to End of Write	20	—	25	—	30	—	35	—	ns
tAS	Address Set-up Time	0	—	0	—	0	—	0	—	ns
tWP	Write Pulse Width[3]	20	—	25	—	30	—	35	—	ns
tWR	Write Recovery Time	5	—	5	—	5	—	5	—	ns
tDW	Data Valid to End of Write	15	—	15	—	20	—	20	—	ns
tHZ	Output High Z Time[1, 2]	—	15	—	15	—	15	—	20	ns
tDH	Data Hold Time	0	—	0	—	0	—	0	—	ns
tWZ	Write Enabled to Output in High Z[1, 2]	—	15	—	15	—	15	—	20	ns
tOW	Output Active from End of Write[1, 2]	0	—	0	—	0	—	0	—	ns
tWDD	Write Pulse to Data Delay[4]	—	45	—	50	—	55	—	65	ns
tDDD	Write Data Valid to Read Data Delay[4]	—	35	—	40	—	45	—	55	ns
BUSY INPUT TIMING										
tWB	Write to $\overline{BUSY}$[5]	0	—	0	—	0	—	0	—	ns
tWH	Write Hold After $\overline{BUSY}$[6]	15	—	20	—	20	—	20	—	ns

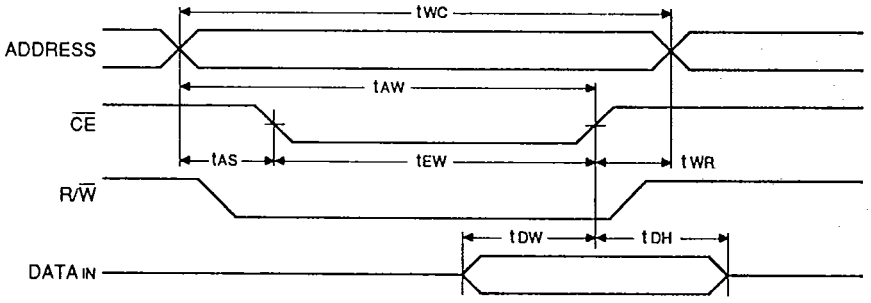
2698 tbl 11

NOTES:
1. Transition is measured ±500mV from low or high impedance voltage with load (Figures 1 and 2).
2. This parameter is guaranteed but not tested.
3. Specified for $\overline{OE}$ at high (refer to "Timing Waveform of Write Cycle", Note 7).
4. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Read with Port-to-Port Delay".
5. To ensure that the write cycle is inhibited during contention.
6. To ensure that a write cycle is completed after contention.
7. 0°C to +70°C temperature range only.

TIMING WAVEFORM OF WRITE CYCLE NO. 1, R/$\overline{W}$ CONTROLLED TIMING(1, 2, 3, 7)

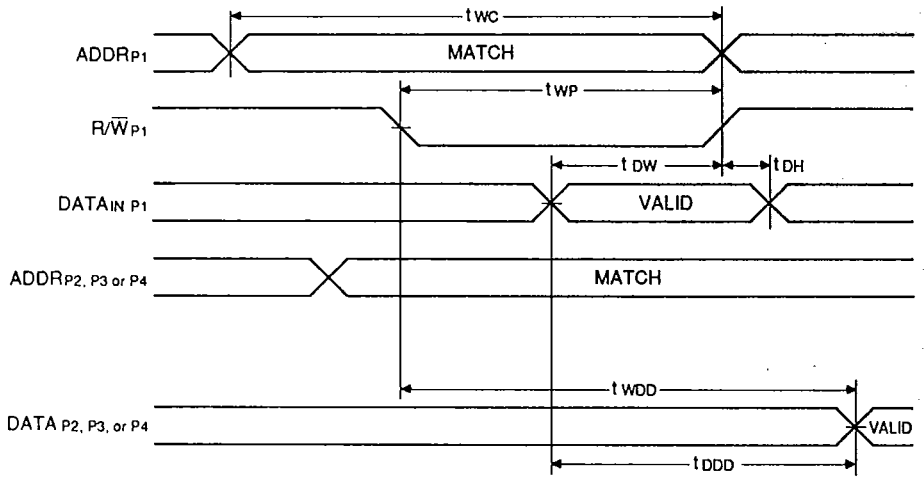


TIMING WAVEFORM OF WRITE CYCLE NO. 2, $\overline{CE}$ CONTROLLED TIMING(1, 2, 3, 5)



NOTES:
1. R/$\overline{W}$ or $\overline{CE}$ must be high during all address transitions.
2. A write occurs during the overlap (tEW or tWP) of a low $\overline{CE}$ and a low R/$\overline{W}$.
3. tWR is measured from the earlier of $\overline{CE}$ or R/$\overline{W}$ going high to the end of write cycle.
4. During this period, the I/O pins are in the output state, and input signals must not be applied.
5. If the $\overline{CE}$ low transition occurs simultaneously with or after the R/$\overline{W}$ low transition, the outputs remain in the high impedance state.
6. Transition is measured ±500mV from steady state with a 5pF load (including scope and jig). This parameter is sampled and not 100% tested.
7. If $\overline{OE}$ is low during a R/$\overline{W}$ controlled write cycle, the write pulse width must be the larger of tWP or (tWZ + tDW) to allow the I/O drivers to turn off data to be placed on the bus for the required tDW. If $\overline{OE}$ is high during an R/$\overline{W}$ controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified tWP.

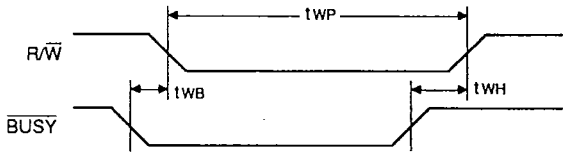
TIMING WAVEFORM OF READ WITH PORT-TO-PORT DELAY(1, 2, 3)



2698 drw 10

NOTES:
1. Assume $\overline{BUSY}$ input at HI and $\overline{CE}$ at LO for the writing port.
2. Write cycle parameters should be adhered to in order to ensure proper writing.
3. Device is continuously enabled for any of the reading ports which has its $\overline{OE}$ at LO.

TIMING WAVEFORM OF WRITE WITH $\overline{BUSY}$ INPUT



2674 drw 11

FUNCTIONAL DESCRIPTION

The IDT7052 provides four ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. These devices have an automatic power down feature controlled by $\overline{CE}$. The $\overline{CE}$ controls on-chip power down circuitry that permits the respective port to go into standby mode when not selected ($\overline{CE}$ high). When a port is enabled, access to the entire memory array is permitted. Each port has its own Output Enable control ($\overline{OE}$). In the read mode, the port's $\overline{OE}$ turns on the output drivers when set LOW. READ/WRITE conditions are illustrated in the table below.

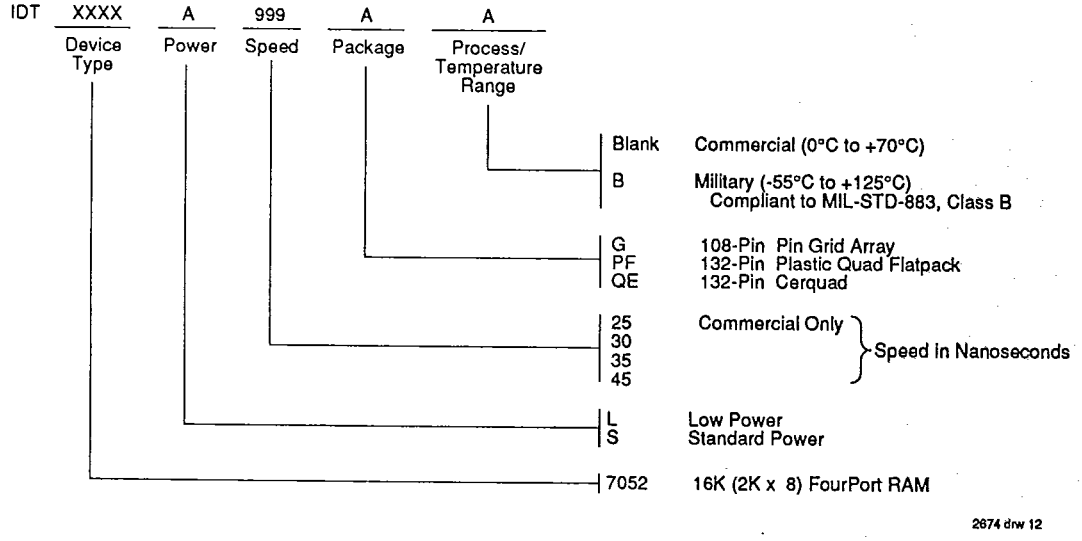
TABLE I – READ/WRITE CONTROL

Any Port[1]				
R/$\overline{W}$	$\overline{CE}$	$\overline{OE}$	D_{0-7}	Function
X	H	X	Z	Port Disabled and in Power Down Mode
X	H	X	Z	$\overline{CE}_{P1} = \overline{CE}_{P2} = \overline{CE}_{P3} = \overline{CE}_{P4}$ = H Power Down Mode, I_{SB} or I_{SB1}
L	L	X	$DATA_{IN}$	Data on port written into memory[2,3]
H	L	L	$DATA_{OUT}$	Data in memory output on port
X	X	H	Z	High impedance outputs

2698 tbl 12

NOTES:
1. H = HIGH, L = LOW, X = Don't Care, Z = High Impedance
2. If $\overline{BUSY}$ = LOW, data is not written.
3. For valid write operation, no more than one port can write to the same address location at the same time.

ORDERING INFORMATION



2674 drw 12